Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	Customer supplied material
	2.0	Primary Flat Orientation	{110} +/- 1 degree	Customer supplied material
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Customer supplied material
	4.0	Secondary Flat Orientation	none or SEMI Standard	Customer supplied material
	5.0	Overall Thickness	600.00 +/- 10.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	SFQR	<1um (10mm*10mm site size)	Guaranteed by process
	8.0	Bow	<40.00µm	ADE to ASTM F534, 100%
	9.0	Warp	<40.00µm	ADE to ASTM F534, 100%
	10.0	Edge Chips	0	Bright Light, 100%
	11.0	Edge Exclusion	5mm	
HandleSilicon	12.0	Handle Growth Method	CZ	Customer supplied material
	13.0	Handle Orientation	{100} +/- 0.5 degree	Customer supplied material
	14.0	Handle Thickness	594.00 +/- 9.00 µm	ADE, 100%
	15.0	Handle Doping Type	P	Customer supplied material
	16.0	Handle Dopant	Boron	Customer supplied material
	17.0	Handle Resistivity	Any	Customer supplied material
	18.0	Backside Finish	Polished with oxide and lasermark	Guaranteed by process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	20,000.00 +/- 1,000.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Device and/or Handle	
DeviceSilicon	22.0	Device Growth Method	CZ	Customer supplied material
	23.0	Device Orientation	{100} +/- 0.5 degree	Customer supplied material
	24.0	Nominal Thickness	4.00 +/- 0.50 µm	Filmetrics 9pts, 100% (note3)
	25.0	Distance to device silicon edge from wafer edge	< 2mm	Typical by Process
	26.0	Device Doping Type	P	Customer supplied material
	27.0	Device Dopant	Boron	Customer supplied material
	28.0	Device Resistivity	10~30 Ohm-cm	Customer supplied material
	29.0	Resisitivity variation (within wafer)	RRV< 10%	Customer supplied material
	30.0	LPD Count	<30pcs @ 0.3um	LPD count
	31.0	Surface	Polished, <0.3nm roughness	Guaranteed by process
	32.0	Top surface Metal Contamination	<5 e10 / cm2	Customer supplied material
	33.0	Oxygen Concentration	<1 e17 / cm3	Customer supplied material
	34.0	Carbon Concentration	<5 e16 / cm3	Customer supplied material

Part Number	Customer

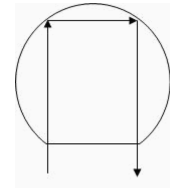
Category		Parameter	Specification	Measurement Method
DeviceSilicon	35.0	Surface Voids	None > 0.5mm	Bright Light, 100% (note2)
	36.0	Haze	None	Bright Light, 100% (note2)
	37.0	Scratches	none on the front-side	Bright Light, 100% (note2)

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

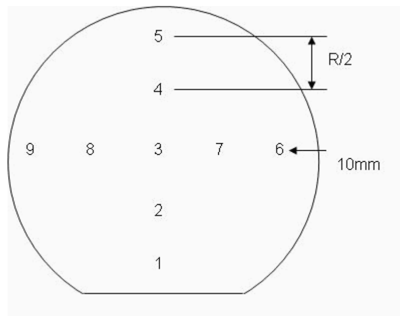
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information